

# Self-masking of spontaneous symmetry breaking in layer materials

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We study  $d$ -wave Fermi surface deformations ( $d$ FSD), the so-called Pomeranchuk instability, on bilayer and infinite-layer square lattices. Since the order parameter of the  $d$ FSD has Ising symmetry, there are two stacking patterns along the  $c$  axis:  $(+, +)$  and  $(+, -)$ . We find that, as long as the  $c$  axis dispersion is finite at the saddle points of the in-plane band dispersion, the  $(+, -)$  stacking is usually favored independently on the details of interlayer coupling, yielding no macroscopic anisotropy. The  $d$ FSD provides unique spontaneous symmetry breaking that is self-masked in layer materials.

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Spontaneous symmetry breaking is a key concept in physics. Typical examples in condensed matter are crystallization, ferromagnetism, antiferromagnetism, ferroelectricity, and superconductivity. Recently a new type of symmetry breaking was found in the shape of the Fermi surface (FS) [1, 2]. The FS usually fulfills the point-group symmetry of the underlying lattice structure. However, it was shown that such symmetry of the FS can be broken by electron correlation effects in the two-dimensional (2D)  $t$ - $J$  [1, 3, 4] and Hubbard [2, 5, 6, 7] models on a square lattice: The FS expands along the  $k_x$  direction and shrinks along the  $k_y$  direction, or vice versa. This instability is characterized by a  $d$ -wave order parameter and we refer to it as  $d$ -wave Fermi surface deformations ( $d$ FSD) or  $d$ -wave Pomeranchuk instability.

The  $d$ FSD state has the same symmetry as the electronic nematic state [8]. Implications of such reduced symmetry were widely discussed for high- $T_c$  cuprates [9]. In particular, the strong  $ab$ -anisotropy of magnetic excitation spectrum observed for untwinned  $\text{YBa}_2\text{Cu}_3\text{O}_y$  [10] was well explained in terms of the  $d$ FSD and its competition with singlet pairing [11]. Moreover many peculiar features observed for the bilayer ruthenate  $\text{Sr}_3\text{Ru}_2\text{O}_7$  [12, 13] also turned out to be well captured in terms of the  $d$ FSD instability [14, 15, 16, 17].

The  $d$ FSD is expected in layer materials, which are characterized by weak interlayer coupling. Since the order parameter of the  $d$ FSD has Ising symmetry, the interlayer coupling drives two possible stacking patterns between the layers,  $(+, +)$  and  $(+, -)$ ; we call the former *ferro-type* (F) stacking and the latter *antiferro-type* (AF). In the latter case, macroscopic anisotropy does not appear, leading to self-masking of the underlying  $d$ FSD instability.

In this Letter, we propose a microscopic theory for the  $d$ FSD phenomenon in realistic layer materials. We find that AF  $d$ FSD state is usually favored independently on the details of interlayer coupling. Thus the  $d$ FSD instability provides unique spontaneous symmetry breaking that is self-masked macroscopically. This generic conclusion is applicable to a wide range of layer materials, including recently discovered iron-based superconductors [18, 19].

We consider both bilayer and infinite-layer models. We

first focus on a bilayer square lattice and analyze the following pure forward scattering model,

$$H = \sum_{\substack{\mathbf{k}, \sigma \\ i=A, B}} (\epsilon_{\mathbf{k}} - \mu) c_{\mathbf{k}\sigma}^{i\dagger} c_{\mathbf{k}\sigma}^i + \frac{1}{2N} \sum_{\substack{\mathbf{k}, \mathbf{k}' \\ i=A, B}} f_{\mathbf{k}\mathbf{k}'} n_{\mathbf{k}}^i n_{\mathbf{k}'}^i + \sum_{\mathbf{k}, \sigma} \epsilon_{\mathbf{k}}^z (c_{\mathbf{k}\sigma}^{A\dagger} c_{\mathbf{k}\sigma}^B + c_{\mathbf{k}\sigma}^{B\dagger} c_{\mathbf{k}\sigma}^A), \quad (1)$$

where  $c_{\mathbf{k}\sigma}^{i\dagger} (c_{\mathbf{k}\sigma}^i)$  creates (annihilates) an electron with momentum  $\mathbf{k}$  and spin  $\sigma$  on the  $i = A$  and  $B$  planes;  $n_{\mathbf{k}}^i = \sum_{\sigma} c_{\mathbf{k}\sigma}^{i\dagger} c_{\mathbf{k}\sigma}^i$  is the number operator;  $N$  is the total number of sites on the  $i$  plane and  $\mu$  is the chemical potential. For hopping amplitudes  $t$  and  $t'$  between nearest and next-nearest neighbors on the square lattice,  $\epsilon_{\mathbf{k}}$  is given by  $\epsilon_{\mathbf{k}} = -2t(\cos k_x + \cos k_y) - 4t' \cos k_x \cos k_y$ . The forward scattering interaction,  $f_{\mathbf{k}\mathbf{k}'} = -gd_{\mathbf{k}}d_{\mathbf{k}'}$ , drives the  $d$ FSD instability, where  $d_{\mathbf{k}} = \cos k_x - \cos k_y$  and  $g > 0$  [20, 21]. The last term in Hamiltonian (1) is the hybridization between A and B planes. We consider three types of  $c$  axis dispersions,  $\epsilon_{\mathbf{k}}^z = -t_z$ ,  $-2t_z(\cos k_x + \cos k_y)$ , and  $-4t_z \cos \frac{k_x}{2} \cos \frac{k_y}{2}$ ; the latter two dispersions vanish at  $\mathbf{k} = (\pi, 0)$  and  $(0, \pi)$  while the former does not. This difference is crucial to the stacking of the  $d$ FSD.

Hamiltonian (1) is analyzed in the Hartree approximation, which becomes exact in the thermodynamic limit in our model. We obtain the mean field

$$\eta^{A(B)} = -\frac{g}{N} \sum_{\mathbf{k}} d_{\mathbf{k}} \langle n_{\mathbf{k}}^{A(B)} \rangle, \quad (2)$$

which is nonzero only if the electronic state loses the four-fold symmetry of the square lattice and is thus the order parameter of the  $d$ FSD in the  $A(B)$  plane. The FS is elongated along the  $k_x$  and  $k_y$  directions for  $\eta^{A(B)} > 0$  and  $\eta^{A(B)} < 0$ , respectively, i.e., the order parameter has Ising symmetry. AF (F) stacking is defined by  $\eta^A \eta^B < 0 (> 0)$ . We determine the mean fields self-consistently under the constraint that each plane has the same electron density. We choose  $t'/t = 0.35$  [16, 22] and  $t_z/t = 0.1$  [22], which is appropriate for the bilayer ruthenate.  $\epsilon_{\mathbf{k}}$  has saddle points in  $\mathbf{k} = (\pi, 0)$  and  $(0, \pi)$ , and thus the van Hove energy of  $\epsilon_{\mathbf{k}}$  is given by  $\mu_{\text{vH}}^0 = 4t' = 1.4t$ . In the following we set  $t = 1$  and shift the energy such that  $\mu_{\text{vH}}^0 \equiv 0$ .

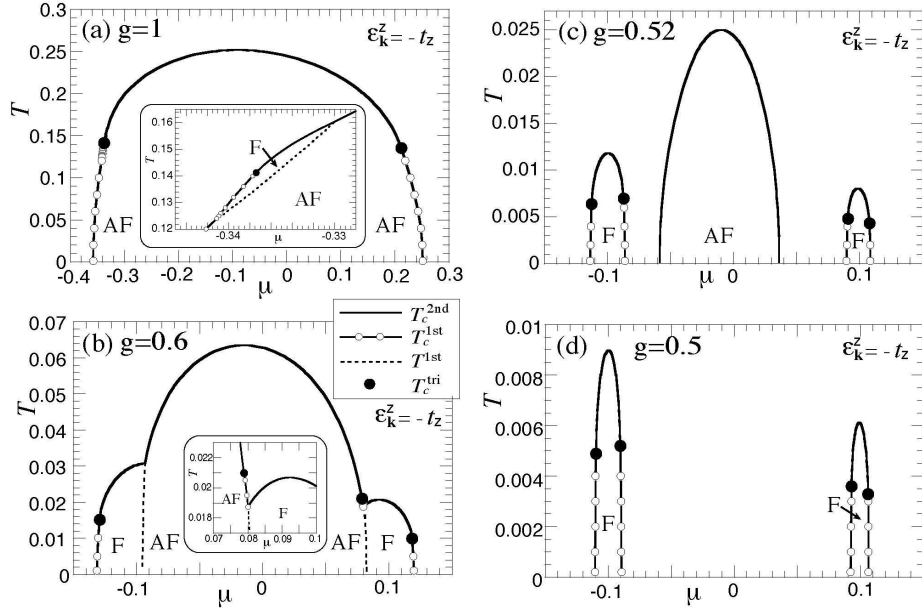


FIG. 1:  $\mu$ - $T$  phase diagrams in the bilayer model with  $\epsilon_{\mathbf{k}}^z = -t_z$  for several choices of  $g$  at  $t_z = 0.1$ . Solid lines,  $T_c^{2nd}$ , denote second order transitions, while first order transitions are denoted by open circles,  $T_c^{1st}$ , and dotted lines,  $T^{1st}$ ; the latter, present in panels (a) and (b), corresponds to a transition between F and AF; solid circles represent tricritical points. The insets magnify the regions around  $\mu \approx -0.33$  and  $T \approx 0.15$  in (a), and around  $\mu \approx 0.08$  and  $T \approx 0.02$  in (b).

We first consider the  $c$  axis dispersion,  $\epsilon_{\mathbf{k}}^z = -t_z$ , from which we can extract a generic conclusion about the stacking of the  $d$ FSD. Figure 1(a) shows the phase diagram obtained for  $g = 1$ . The  $d$ FSD instability occurs around the van Hove energy of the in-plane dispersion, i.e.  $\mu=0$  as in the case of the single-layer model (Ref. 21);  $T_c$  is almost unchanged by the presence of  $\epsilon_{\mathbf{k}}^z$ . The AF  $d$ FSD state, namely  $\eta^A = -\eta^B \neq 0$ , is stable in most of the region of the phase diagram. The F stacking appears in a very small region, as shown in the inset of Fig. 1(a). When the coupling constant  $g$  is reduced, the F regions increase, close to the edges of the transition line. Yet the AF region is still much larger than the F ones, as it is shown in Fig. 1(b). Upon further reducing  $g$ , the F and AF regions split from one another [Fig. 1(c)]. After this “intermediate” phase, the property of the phase diagram drastically changes below  $g = 0.5$ , as shown in Fig. 1(d): No  $d$ FSD instability appears around  $\mu=0$ , but the transition occurs around the van Hove energy of the bonding and antibonding bands, namely around  $\mu_{\text{vH}} = \pm t_z = \pm 0.1$ . The phase diagram eventually contains only F regions. This property does not change down to an infinitesimally small  $g$ .

To gain an understanding of the  $d$ FSD stacking, we consider the Landau expansion of the grand canonical potential (per lattice site) with respect to  $\eta^A$  and  $\eta^B$ ,

$$\omega(\eta^A, \eta^B) = \frac{T}{2} [(\eta^A)^2 + (\eta^B)^2] + \mathcal{J}\eta^A\eta^B + \dots \quad (3)$$

The condition,  $\mathcal{I}^2 - \mathcal{J}^2 = 0$ , determines a second order transition.  $\mathcal{J}$  drives AF and F stacking for  $\mathcal{J} > 0$  and

$\mathcal{J} < 0$ , respectively, and is given by

$$\mathcal{J} = \frac{1}{2N} \sum_{\mathbf{k}} d_{\mathbf{k}}^2 \left\{ f'(\lambda_{\mathbf{k}}^+) + f'(\lambda_{\mathbf{k}}^-) - \frac{f(\lambda_{\mathbf{k}}^+) - f(\lambda_{\mathbf{k}}^-)}{\epsilon_{\mathbf{k}}^z} \right\}, \quad (4)$$

where  $\lambda_{\mathbf{k}}^{\pm} = \epsilon_{\mathbf{k}} - \mu \pm \epsilon_{\mathbf{k}}^z$  is the dispersion of the bonding and antibonding bands;  $f(\lambda) = (e^{\lambda/T} + 1)^{-1}$  is the Fermi function at temperature  $T$  and  $f'$  is its derivative.

As long as a second order transition occurs around  $\mu=0$  [Figs. 1(a) and (b)], we can analyze Eq. (4) by expanding it with respect to  $\epsilon_{\mathbf{k}}^z$  and obtain

$$\mathcal{J} = \frac{1}{3} \frac{\partial^2}{\partial \mu^2} \int d\epsilon N_d^z(\epsilon) f'(\epsilon - \mu) \quad (5)$$

where

$$N_d^z(\epsilon) = \frac{1}{N} \sum_{\mathbf{k}} d_{\mathbf{k}}^2 (\epsilon_{\mathbf{k}}^z)^2 \delta(\epsilon_{\mathbf{k}} - \epsilon). \quad (6)$$

Since the  $\mathbf{k}$  summation in Eq. (6) is dominated by the contribution from the saddle points of  $\epsilon_{\mathbf{k}}$ , we expand  $\epsilon_{\mathbf{k}}$  and  $\epsilon_{\mathbf{k}}^z$  around the saddle points.  $\epsilon_{\mathbf{k}}$  is then written as  $\epsilon_{\mathbf{k}} = \frac{k_+ k_-}{2m}$  after choosing a suitable choice of momentum variables  $k_+$  and  $k_-$  with a cutoff momentum  $\Lambda$ , namely  $|k_{\pm}| < \Lambda$ ;  $m$  is related to  $t$  and  $t'$ ;  $d_{\mathbf{k}}$  is replaced by a constant, which just rescales  $\epsilon_{\mathbf{k}}^z$ , and we set  $d_{\mathbf{k}} = 1$ .

For  $\epsilon_{\mathbf{k}}^z = -t_z$ , Eq. (6) becomes

$$N_d^z(\epsilon) = \frac{2mt_z^2}{\pi^2} \log \frac{\epsilon_{\Lambda}}{|\epsilon|} \quad (7)$$

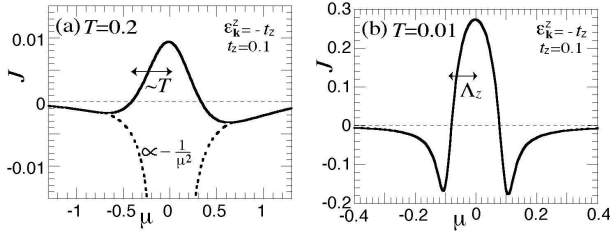


FIG. 2: Coupling constant  $\mathcal{J}$  between  $\eta^A$  and  $\eta^B$  as a function of  $\mu$  at  $T = 0.2$  (a) and  $0.01$  (b) for  $\epsilon_{\mathbf{k}}^z = -t_z$ . In (a), the function of  $-\mu^{-2}$  is also drawn.

where  $\epsilon_\Lambda = \frac{\Lambda^2}{2m}$ . At zero temperature Eq. (5) reads  $\mathcal{J} = -\frac{2mt_z^2}{3\pi^2} \frac{1}{\mu^2}$ . This  $\mu^{-2}$  singularity is, however, cut off at a scale of the order of  $T_c^0$ , the transition temperature at  $\mu = 0$ . Therefore  $\mathcal{J}$  becomes positive for  $|\mu| \lesssim T_c^0$ , as shown in Fig. 2(a). Because of the universal property of the  $d$ FSD instability obtained for a single layer model [21], the  $d$ FSD phase is stabilized in the region  $|\mu| \lesssim T_c^0$ . Therefore the sign of  $\mathcal{J}$  is expected to be positive, leading to AF stacking of the  $d$ FSD in a major region of the phase diagram, as seen in Figs. 1 (a) and (b).

If the coupling constant  $g$  is reduced, the temperature scale of the  $d$ FSD becomes small and the energy scale of  $\epsilon_{\mathbf{k}}^z$  must be taken into account. We consider Eq. (4) instead of its lowest order expansion of Eq. (5). The scale of  $\epsilon_{\mathbf{k}}^z$  is defined as the bilayer splitting at the saddle points of the in-plane dispersion, namely

$$\Lambda_z = |\epsilon_{\mathbf{k}}^z| \text{ at } \mathbf{k} = (\pi, 0) \text{ and } (0, \pi) \quad (8)$$

in the present case and thus  $\Lambda_z = t_z$ . The positive  $\mathcal{J}$  region is bounded by the scale  $\Lambda_z$ , rather than  $T$ , as seen in Fig. 2(b). Then  $\mathcal{J}$  becomes negative for  $|\mu| \gtrsim \Lambda_z$  and shows steep dips at the van Hove energy of the bonding and antibonding bands, i.e. at  $\mu_{\text{vH}} = \pm t_z$ . This structure originates from the singular contribution of  $f'$  in Eq. (4). When the temperature scale becomes much smaller than  $\Lambda_z$ , we have seen that the  $d$ FSD instability occurs around  $\mu = \mu_{\text{vH}}$ . Therefore we obtain F stacking, as seen in Fig. 1(d).

So far we have considered a simple  $c$  axis dispersion. However, the above analysis holds also for other choices of a  $c$  axis dispersion, e.g.  $\epsilon_{\mathbf{k}}^z = -t_z(\cos k_x - \cos k_y)^2$ , as long as  $\Lambda_z \neq 0$ . Hence we obtain a generic conclusion for bilayer systems: F stacking prevails when the temperature scale of the  $d$ FSD is much smaller than  $\Lambda_z$ , otherwise the major stacking is AF [23].

What happens for  $\Lambda_z = 0$ ? This can be seen from the analysis of Eq. (5). When  $\epsilon_{\mathbf{k}}^z$  is expanded as  $\epsilon_{\mathbf{k}}^z = (a_1 k_+ + b_1 k_-)t_z$  around the saddle points of the in-plane band dispersion, the logarithmic singularity in Eq. (7) is weakened to  $\epsilon \log |\epsilon|$ , leading to  $\mathcal{J} \approx \frac{8m^2 t_z^2}{3\pi^2} \frac{a_1 b_1}{\mu}$ . The dispersion in this case may be taken as  $\epsilon_{\mathbf{k}}^z = -4t_z \cos \frac{k_x}{2} \cos \frac{k_y}{2}$ , for which we obtain  $a_1 b_1 < 0$ . The phase diagram indeed showed AF and F stacking for  $\mu < 0$  and  $\mu > 0$ . On the

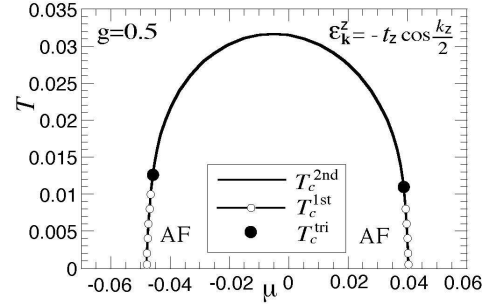


FIG. 3:  $\mu$ - $T$  phase diagram in the infinite-layer model with  $\epsilon_{\mathbf{k}}^z = -t_z \cos \frac{k_z}{2}$  for  $t_z = 0.1$ . The notation is the same as in Fig. 1.

other hand, when  $\epsilon_{\mathbf{k}}^z$  is expanded as  $\epsilon_{\mathbf{k}}^z = (a_2 k_+^2 + b_2 k_-^2 + c_2 k_+ k_-)t_z$ , we obtain  $\mathcal{J} \approx \frac{16m^3 t_z^2}{3\pi^2} (2a_2 b_2 + c_2^2) \log \frac{|\mu|}{\epsilon_\Lambda}$ . Thus F (AF) stacking is stabilized for  $2a_2 b_2 + c_2^2 > 0 (< 0)$ ; for  $\epsilon_{\mathbf{k}}^z = -2t_z(\cos k_x + \cos k_y)$ ,  $\mathcal{J}$  becomes positive, indicating that the major stacking is F. As a conclusion, for  $\Lambda_z = 0$  the stacking of the  $d$ FSD depends on the precise form of  $\epsilon_{\mathbf{k}}^z$ .

To gain more insight into the physics of layer materials, we now analyze an infinite-layer model. This is given by the same Hamiltonian (1) except that  $t_z$  is replaced by  $t_z \cos \frac{k_z}{2}$  and the  $\mathbf{k}$  summation is taken also for  $k_z$ ; here we assume two layers per unit cell. The conclusions obtained from Eq. (5) still hold, since the  $k_z$  dependence appears only in  $\epsilon_{\mathbf{k}}^z$  in Eq. (6) and just yields a factor of  $\frac{1}{2}$  after the  $k_z$  summation. AF stacking is thus stabilized in a major region of the phase diagram for  $\Lambda_z \neq 0$ . Unlike the situation in the bilayer model, bonding and antibonding bands now depend on  $k_z$ . In this case, even if the temperature scale of the  $d$ FSD becomes very small, the instability still occurs around  $\mu = 0$  [24]. The analysis of Eq. (5) then holds, yielding AF stacking [Fig. 3].

We have focused on a  $c$  axis dispersion, which is certainly a relevant interlayer coupling in metallic systems. There may be other couplings such as Coulomb interaction  $\sum_{i,j} V_{ij}^z n_i^A n_j^B$  and spin-spin interaction  $\sum_{i,j} J_{ij}^z \mathbf{S}_i^A \cdot \mathbf{S}_j^B$ . However, these interactions do not yield a direct coupling between  $\eta^A$  and  $\eta^B$ . They may just shift the chemical potential and renormalize the  $c$  axis dispersion, which is indeed the case in the Hartree-Fock approximation, as long as the in-plane interaction  $f_{\mathbf{k}\mathbf{k}'}$  is dominant.

While our Hamiltonian (1) is simple, it is known that a forward scattering model works very well for  $\text{Sr}_3\text{Ru}_2\text{O}_7$  [14, 15, 16, 17] and that such a forward scattering interaction turns out to be inherent in the  $t$ - $J$  [1, 3, 4] and Hubbard [2, 5, 6, 7] models, minimal models for cuprate superconductors. In addition, although the symmetry is different from the  $d$ FSD, a forward scattering model is also known to work for  $\text{URu}_2\text{Si}_2$  [25].

The bilayer ruthenate  $\text{Sr}_3\text{Ru}_2\text{O}_7$  is a promising material for the  $d$ FSD instability [12, 13]. LDA calculations [22] show that the intrabilayer dispersion does not van-

ish at the saddle points  $\mathbf{k} = (\pi, 0)$  and  $(0, \pi)$ , that is  $\Lambda_z \neq 0$ . Since the temperature scale of the  $d$ FSD is about 1 K and is much smaller than  $\Lambda_z$  [22], we expect F  $d$ FSD stacking within each bilayer. On the other hand, there is a very weak interbilayer dispersion, which is expected to have the form factor  $t'_z \cos \frac{k_x}{2} \cos \frac{k_y}{2}$  because the Ru sites shift by  $(\frac{1}{2}, \frac{1}{2})$  between adjacent bilayers. The interbilayer dispersion thus vanishes at  $\mathbf{k} = (\pi, 0)$  and  $(0, \pi)$ , i.e.  $\Lambda_z = 0$ . In this case,  $\mathcal{J}$  is estimated as  $\mathcal{J} \sim -1/\mu$  as calculated above. This suggests AF and F stacking between adjacent bilayers, namely the stacking  $(++, --, ++, --, \dots)$  and  $(++, ++, ++, ++, \dots)$  for  $\mu \lesssim 0$  and  $\mu \gtrsim 0$  [26], respectively.

High-temperature cuprate superconductors are also promising materials for the  $d$ FSD instability [10]. While competition with singlet pairing may suppress the instability, the  $d$ FSD is still important, yielding strong correlations [1, 4], which may lead to a giant anisotropic response to a small external anisotropy, e.g. lattice anisotropy. Hence the stacking is determined by the external anisotropy and we expect F stacking for Y-based cuprates [11] and AF stacking in La-based cuprates in the low temperature tetragonal structure [1].

We have studied a generic tendency for the  $d$ FSD stacking in bilayer and infinite-layer models. We have found that the stacking does not depend on the details of interlayer coupling as long as the  $c$  axis dispersion is finite at the saddle points of the in-plane band dispersion,

namely as long as  $\Lambda_z \neq 0$ . For bilayer systems we have found F stacking only when the temperature scale of the  $d$ FSD is much smaller than  $\Lambda_z$  [Fig. 1(d)], and AF stacking otherwise [Figs. 1(a)-(c)]. For infinite-layer systems instead the major stacking pattern is always AF [Fig. 3].

The  $d$ FSD instability is a generic tendency in correlated electron systems as found in different theoretical models [1, 2, 5, 27]. The  $d$ FSD is thus expected for various materials except if other instabilities prevail over the  $d$ FSD instability. Since the condition  $\Lambda_z \neq 0$  is fulfilled for most materials unless there is a special symmetry reason, typical materials with a high critical temperature for the  $d$ FSD instability may have AF stacking. While spontaneous symmetry breaking is by definition recognized by symmetry breaking of the system, the  $d$ FSD provides a conceptually interesting property that spontaneous symmetry breaking can be self-masked in realistic materials.

Given the fact that antiferromagnetism was recognized about twenty centuries later than ferromagnetism [28, 29], it is not difficult to believe that the  $d$ FSD instability is hidden in various layer materials. Because of a coupling to the lattice, the easiest step to find AF  $d$ FSD materials is to test a twofold lattice modulation along the  $c$  axis.

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